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October 2014

FCD850N80Z / FCU850N80Z

N-Channel SuperFET® II MOSFET

800 V, 6 A, 850 mΩ

Features

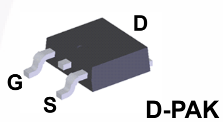
- Typ. $R_{DS(on)}$ = 710 mΩ (Typ.)
- Ultra Low Gate Charge (Typ. Q_g = 22 nC)
- Low E_{oss} (Typ. 2.3 uJ @ 400V)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 106 pF)
- 100% Avalanche Tested
- RoHS Compliant
- ESD Improved Capability

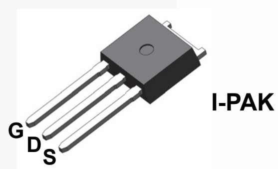
Applications

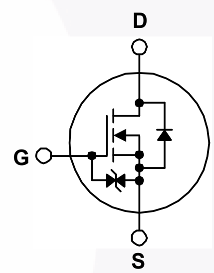
- AC - DC Power Supply
- LED Lighting

Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. In addition, internal gate-source ESD diode allows to withstand over 2kV HBM surge stress.Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as Audio, Laptop adapter, Lighting, ATX power and industrial power applications.







Absolute Maximum Ratings T_C=25°C unless otherwise noted.

Symbol	Parameter		FCD850N80Z FCU850N80Z	Unit
V_{DSS}	Drain to Source Voltage		800	V
V_{GSS}	Gate to Source Voltage	- DC	±20	V
		- AC (f > 1 Hz)	±30	
I_D	Drain Current	- Continuous (T_C = 25°C)	6	A
		- Continuous (T_C = 100°C)	3.8	
I_{DM}	Drain Current	- Pulsed (Note 1)	18	A
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	114	mJ
I_{AR}	Avalanche Current	(Note 1)	1.2	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	0.284	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt	(Note 3)	20	
P_D	Power Dissipation	(T_C = 25°C)	75	W
		- Derate Above 25°C	0.6	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FCD850N80Z FCU850N80Z	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.65	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	100	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCD850N80Z	FCD850N80Z	DPAK	Tape and Reel	330 mm	16 mm	2500 units
FCU850N80Z	FCU850N80Z	IPAK	Tube	NA	NA	75 units

Electrical Characteristics $T_C = 25^oC$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	$V_{GS} = 0$ V, $I_D = 1$ mA, $T_J = 25°C$	800	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 1$ mA, Referenced to 25^oC	-	0.8	-	$V/^oC$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 800$ V, $V_{GS} = 0$ V	-	-	25	μA
		$V_{DS} = 640$ V, $V_{GS} = 0$ V, $T_C = 125^oC$	-	-	250	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm20$ V, $V_{DS} = 0$ V	-	-	±10	μA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 0.6$ mA	2.5	-	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10$ V, $I_D = 3$ A	-	710	850	mΩ
g_{FS}	Forward Transconductance	$V_{DS} = 20$ V, $I_D = 3$ A	-	3.5	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 100$ V, $V_{GS} = 0$ V, f = 1 MHz	-	990	1315	pF
C_{oss}	Output Capacitance		-	28	37	pF
C_{rss}	Reverse Transfer Capacitance		-	0.74	-	pF
C_{oss}	Output Capacitance	$V_{DS} = 480$ V, $V_{GS} = 0$ V, f = 1 MHz	-	15	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0$ V to 480 V, $V_{GS} = 0$ V	-	106	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 640$ V, $I_D = 6$ A, $V_{GS} = 10$ V (Note 4)	-	22	29	nC
Q_{gs}	Gate to Source Gate Charge		-	5	-	nC
Q_{gd}	Gate to Drain “Miller” Charge		-	8.6	-	nC
ESR	Equivalent Series Resistance	f = 1 MHz	-	2.4	-	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 400$ V, $I_D = 6$ A, $V_{GS} = 10$ V, $R_g = 4.7$ Ω (Note 4)	-	16	42	ns
t_r	Turn-On Rise Time		-	10	30	ns
$t_{d(off)}$	Turn-Off Delay Time		-	40	90	ns
t_f	Turn-Off Fall Time		-	4.5	19	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	6	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	18	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0$ V, $I_{SD} = 6$ A	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0$ V, $I_{SD} = 6$ A, $dI_F/dt = 100$ A/μs	-	318	-	ns
Q_{rr}	Reverse Recovery Charge		-	4.5	-	μC

Notes:

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. $I_{AS} = 1.2$ A, $V_{DD} = 50$ V, $R_G = 25$ Ω, Starting $T_J = 25°C$
3. $I_{SD} \le 6$ A, di/dt ≤ 200 A/μs, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25°C$
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

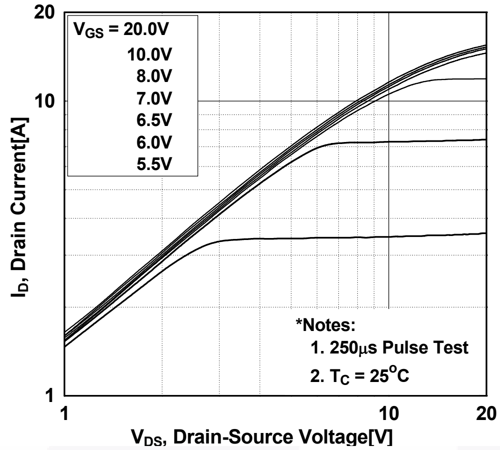


Figure 2. Transfer Characteristics

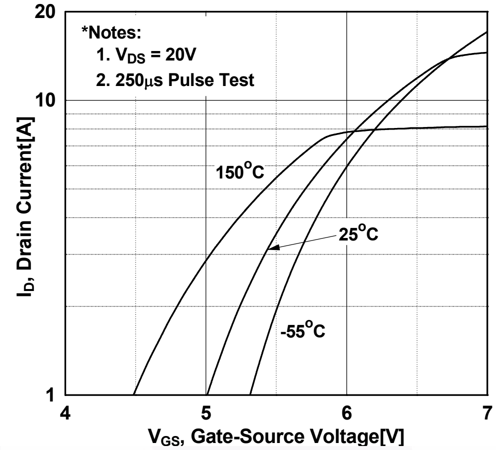


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

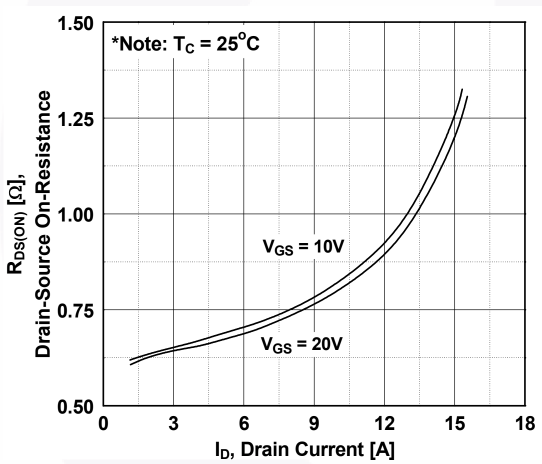


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

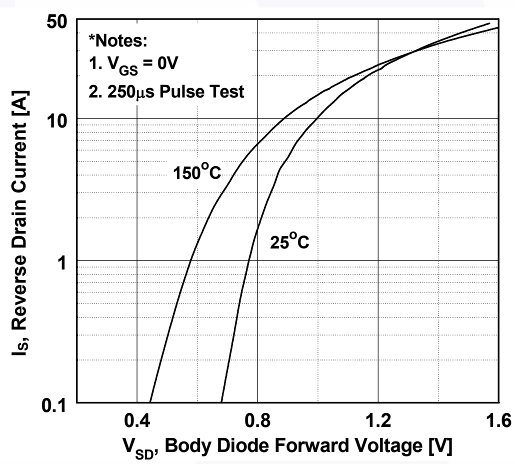


Figure 5. Capacitance Characteristics

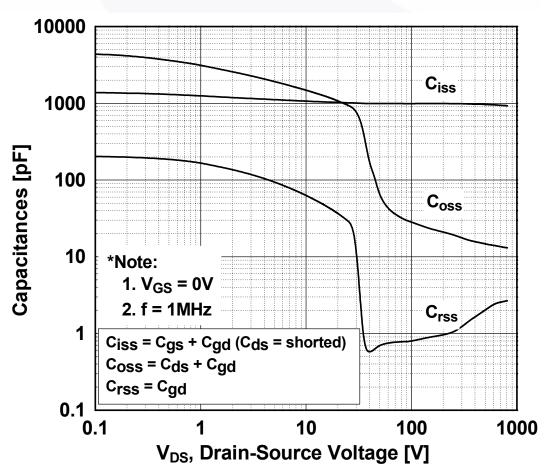
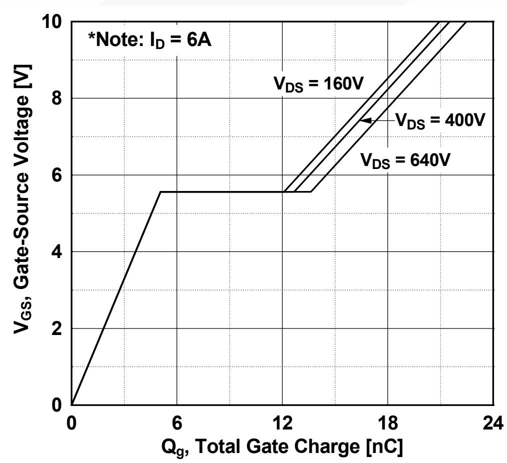


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

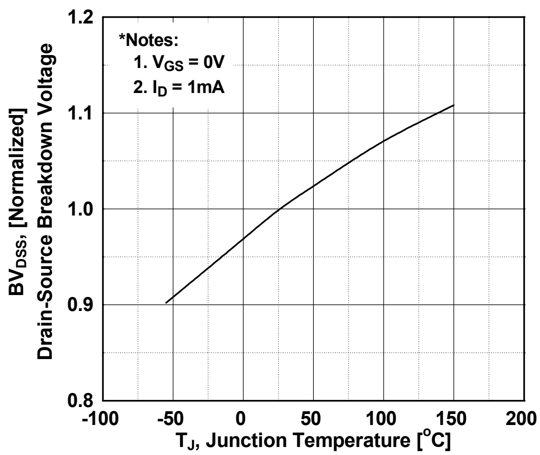


Figure 8. On-Resistance Variation vs. Temperature

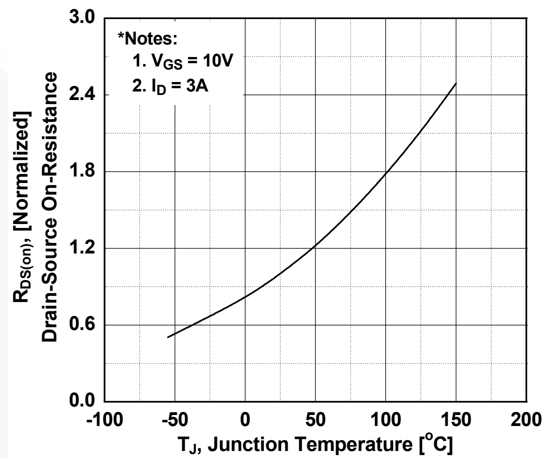


Figure 9. Maximum Safe Operating Area

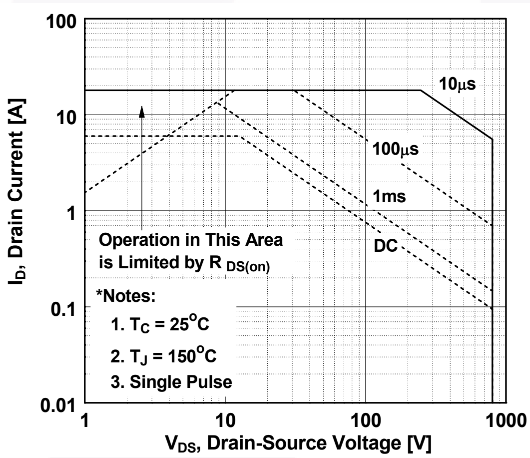


Figure 10. Maximum Drain Current vs. Case Temperature

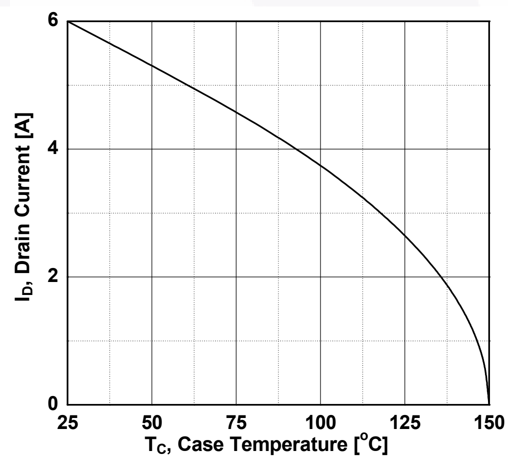
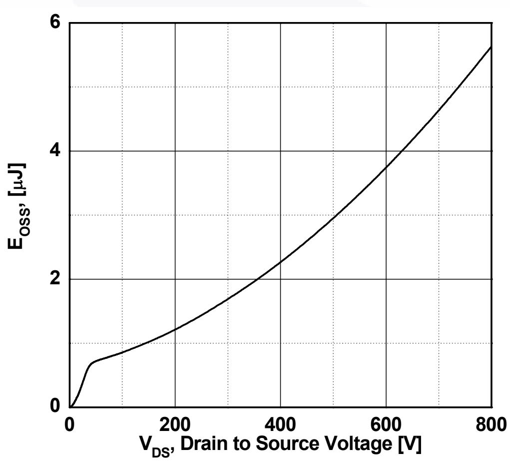
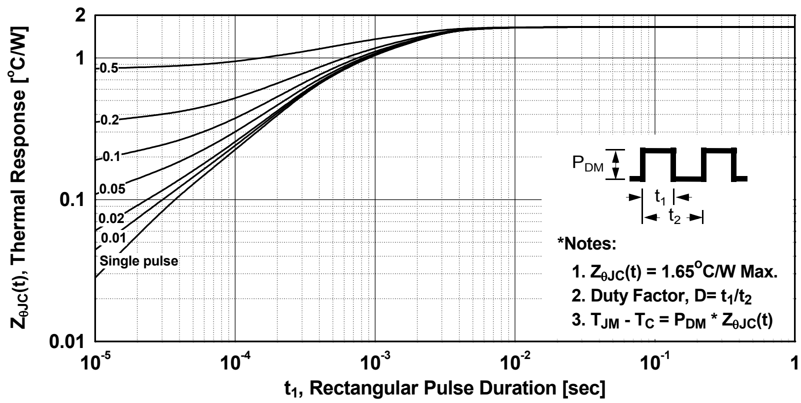


Figure 11. Eoss vs. Drain to Source Voltage



Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



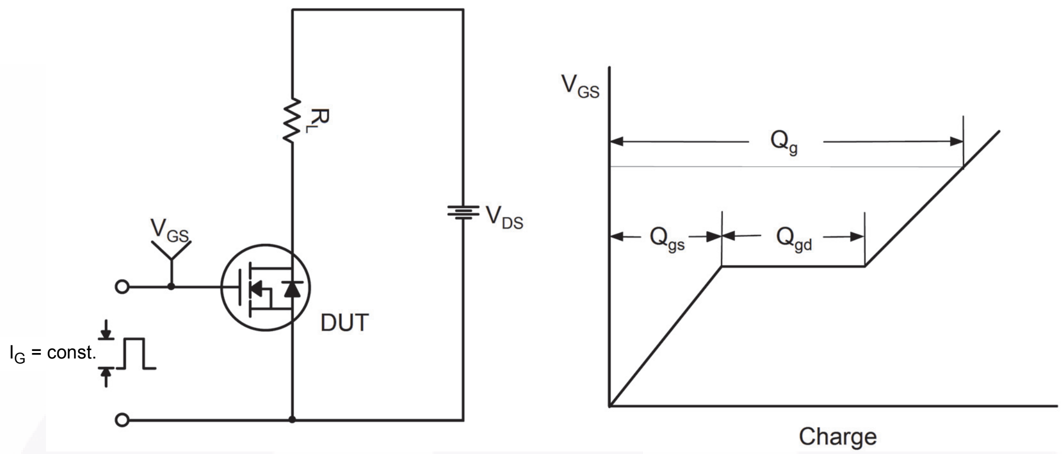


Figure 13. Gate Charge Test Circuit & Waveform

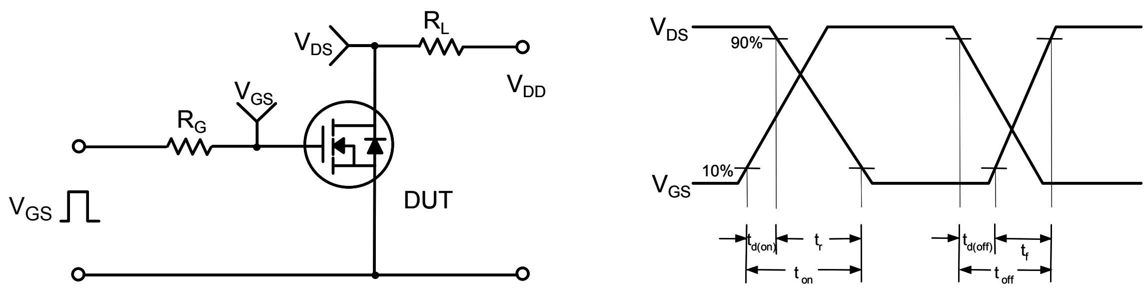


Figure 14. Resistive Switching Test Circuit & Waveforms

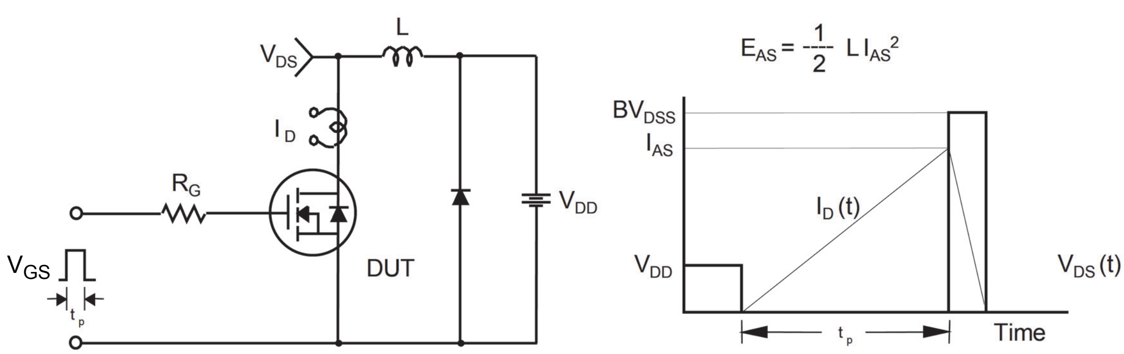


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

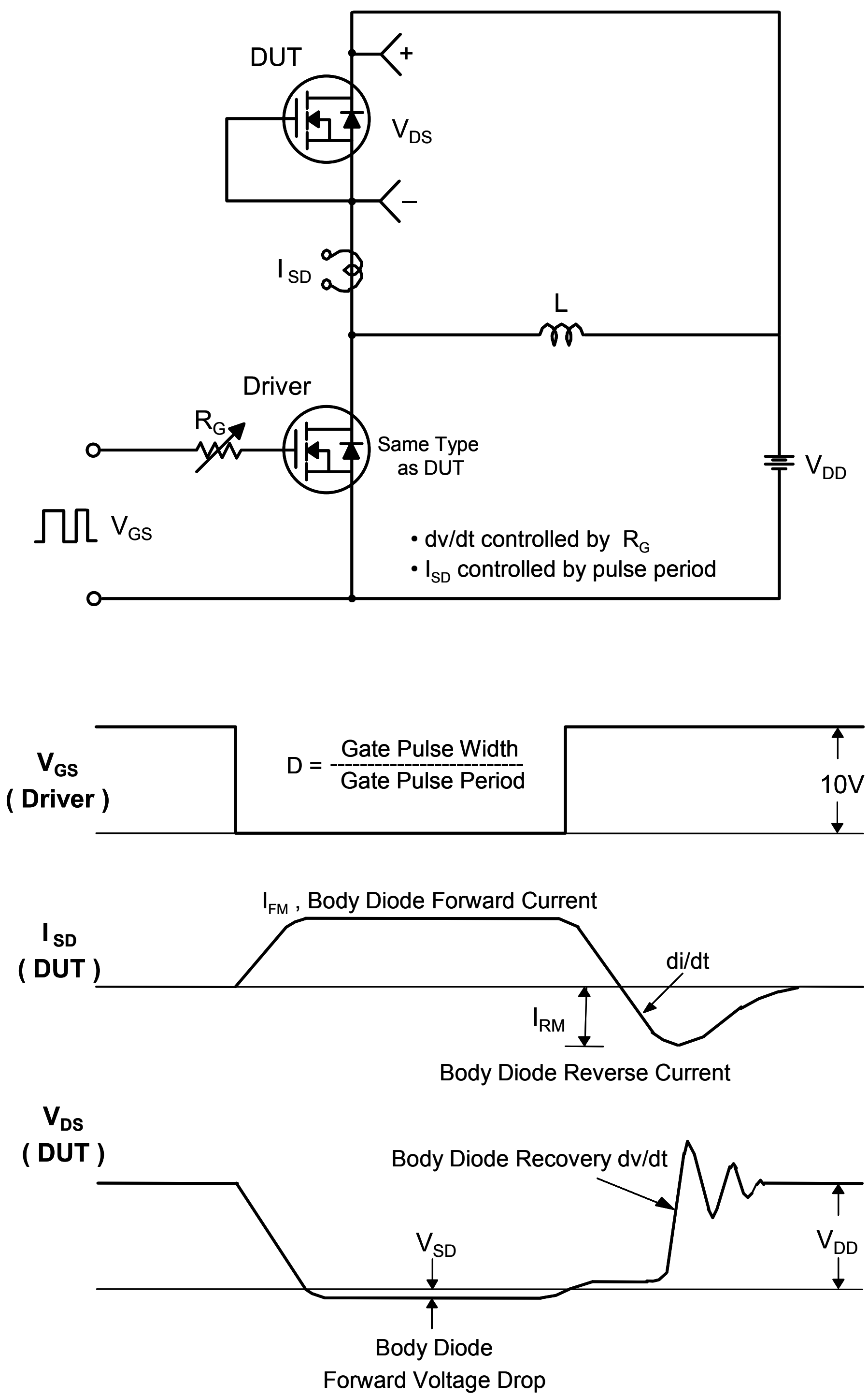
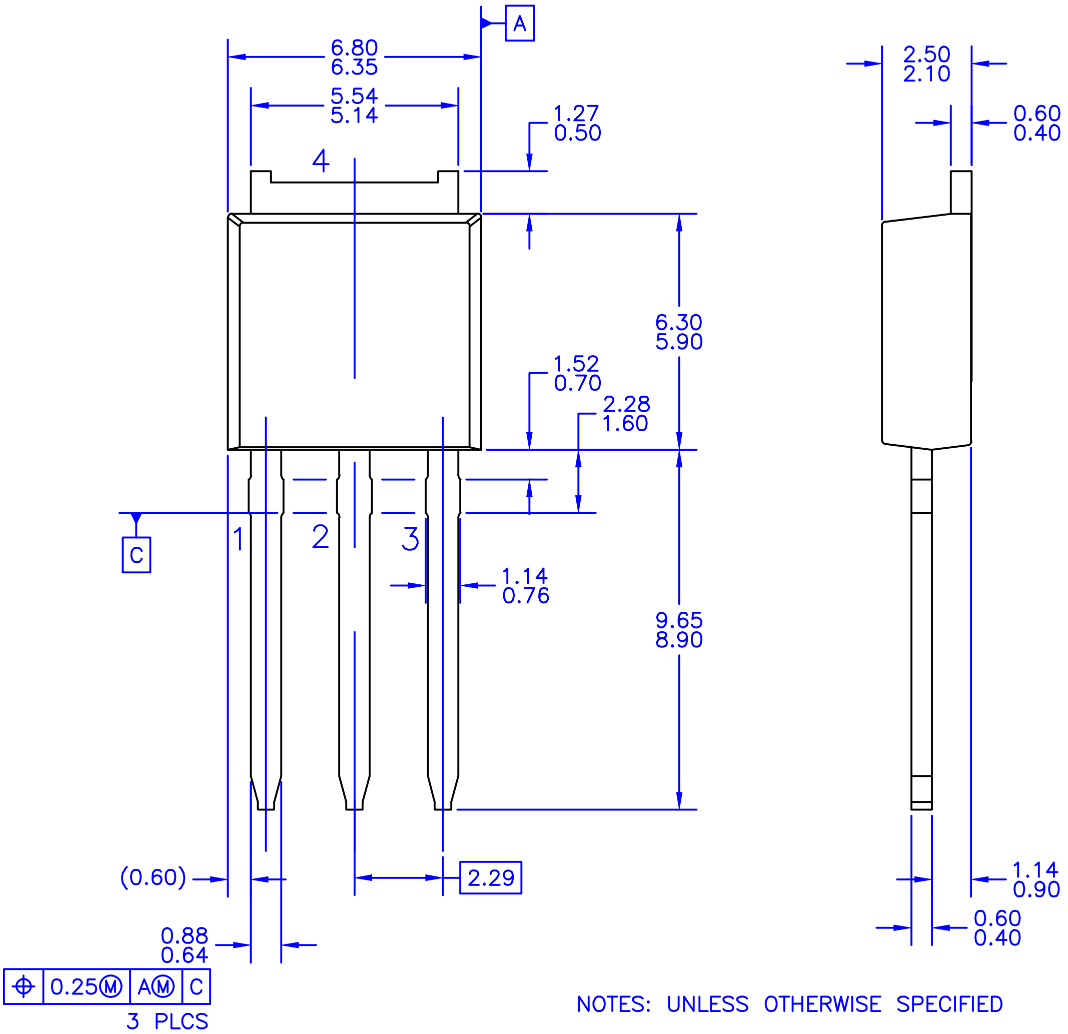
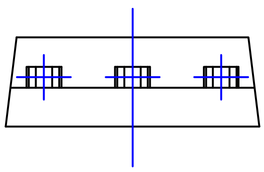


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms





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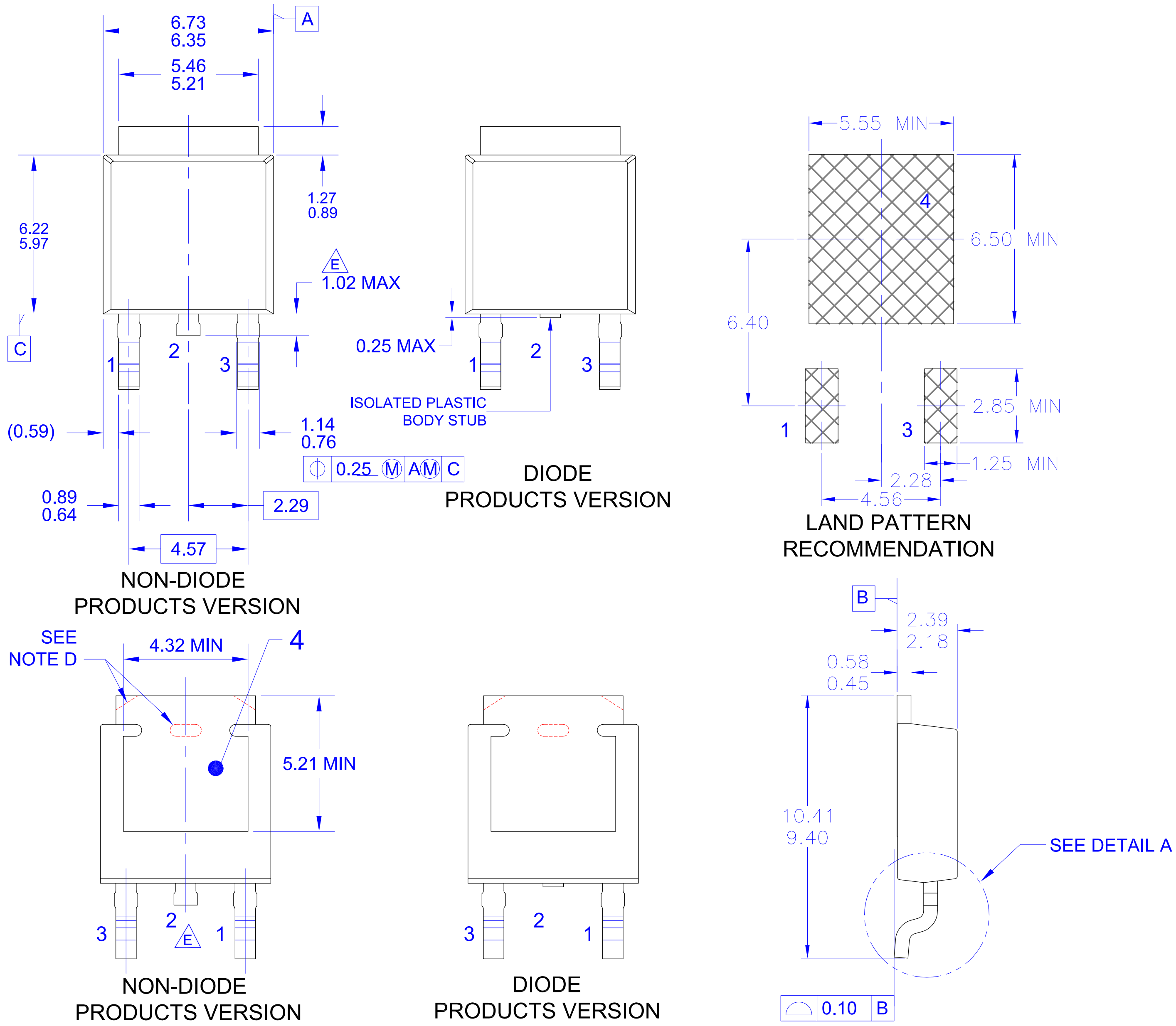

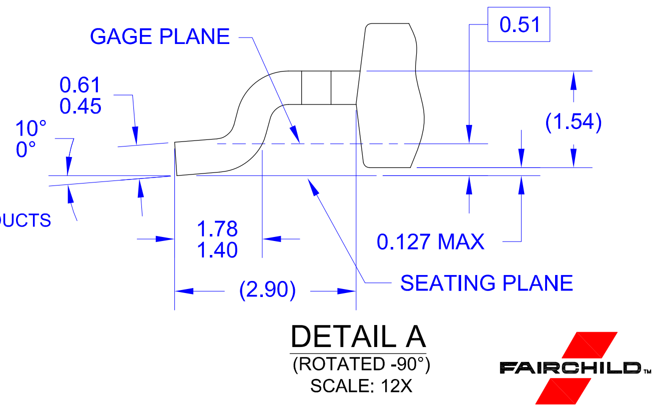

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F) DIMENSIONS ARE EXCLUSIVE OF BURS, MOLD FLASH AND TIE BAR EXTRUSIONS.

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